

<b>L Numb r</b>	<b>Hits</b>	<b>Search Text</b>	<b>DB</b>	<b>Time stamp</b>
<b>108</b>	<b>24107</b>	<b>nucleation</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/05/14 15:23</b>
<b>109</b>	<b>114</b>	<b>nucleation and (reoxide or re-oxide or reoxidation or re-oxidation)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/05/14 15:23</b>
<b>110</b>	<b>69</b>	<b>nucleation and (reoxide or re-oxide or reoxidation or re-oxidation) and nitride</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/05/14 15:24</b>
<b>111</b>	<b>12</b>	<b>nucleation same (reoxide or re-oxide or reoxidation or re-oxidation) same nitride</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/05/14 15:26</b>
<b>112</b>	<b>1</b>	<b>nucleation near10 (reoxide or re-oxide or reoxidation or re-oxidation) near10 nitride</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/05/14 15:24</b>
<b>113</b>	<b>2</b>	<b>nucleation same (reoxide or re-oxide or reoxidation or re-oxidation) same nitride same trap</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/05/14 15:27</b>
<b>-</b>	<b>16</b>	<b>nitride same (re-oxide or reoxide)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/09/03 15:00</b>
<b>-</b>	<b>1</b>	<b>(nitride same (re-oxide or reoxide)).clm.</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/09/03 15:00</b>
<b>-</b>	<b>0</b>	<b>(nitride or SiN) and (reoxide or re-oxide) and (electron near trap)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/09/03 15:01</b>
<b>-</b>	<b>0</b>	<b>(nitride or SiN) and (r oxide or r - xid ) and (electr n near10 trap)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/09/03 15:02</b>

-	16	nitride near oxid near di lectric near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:02
-	435	nitrid near5 xid near5 di l ctric n ar capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:02
-	1	(nitride near5 oxide near5 dielectric near capacitor) and (electron near trap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:07
-	4	(nitride near5 oxide near5 dielectric near capacitor) and (electron near2 (trap or trapping or trapped))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:08
-	3	(nitride adj layer) and ((reoxide or re-oxide) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:09
-	0	((nitride adj layer) and ((reoxide or re-oxide) adj layer)) and (trap or trapped or trapping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:10
-	3	((SiN or nitride) adj layer) and ((reoxide or re-oxide) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:10